

ABSTRACT OF THE DISCLOSURE



08/520079

In a monolithic active matrix circuit formed on a substrate, the active regions of at least a part of the thin film transistors (TFTs) constituting the peripheral circuit for driving the matrix region are added with a metal element for promoting the crystallization of silicon at a concentration of 1×10^{16} to 5×10^{19} cm⁻³, no metal element is added to the active region of the TFTs for the matrix region. The channel forming regions of at least a part of the TFTs constituting the peripheral circuit and the channel forming regions of the TFTs for the matrix region are formed by a silicon semiconductor thin film having a monodomain structure.